

SK35GD126ET

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SEMITOP® 3

IGBT Module

SK35GD126ET

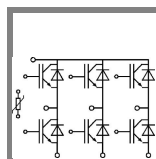
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications

- Inverter

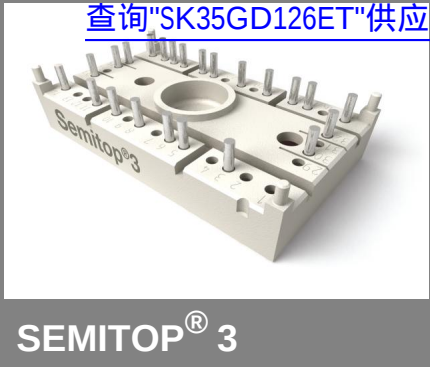


GD-ET

Absolute Maximum Ratings				$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25\text{ °C}$			1200	V
I_C	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$		40	A
		$T_s = 80\text{ °C}$		32	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$			70	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 600\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 1200\text{ V}$			10	μs
Inverse Diode					
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$		34	A
		$T_s = 80\text{ °C}$		23	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$			70	A
Module					
$I_{t(RMS)}$					A
T_{vj}				-40 ... +150	$^{\circ}\text{C}$
T_{stg}				-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.			2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 1,5 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C T _j = 125 °C					mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V T _j = 25 °C T _j = 125 °C				600	nA nA
V _{CE0}	T _j = 25 °C T _j = 125 °C			1 0,9	1,2	V V
r _{CE}	V _{GE} = 15 V T _j = 25°C T _j = 125°C			20 31	26	mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 35 A, V _{GE} = 15 V T _j = 25°C _{chiplev.} T _j = 125°C _{chiplev.}			1,7 2	2,1	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			2,5 0,132 0,115		nF nF nF
t _{d(on)} t _r E _{on}	R _{Gon} = 15 Ω	V _{CC} = 600V I _{Cnom} = 35A		85 30 4,6		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 15 Ω	T _j = 125 °C V _{GE} =±15V		430 90 4,3		ns ns mJ
R _{th(j-s)}	per IGBT				1,05	K/W

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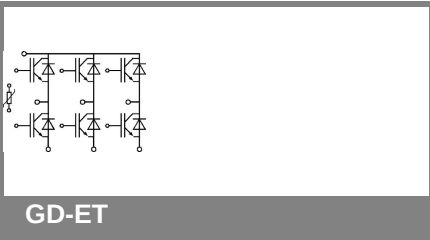
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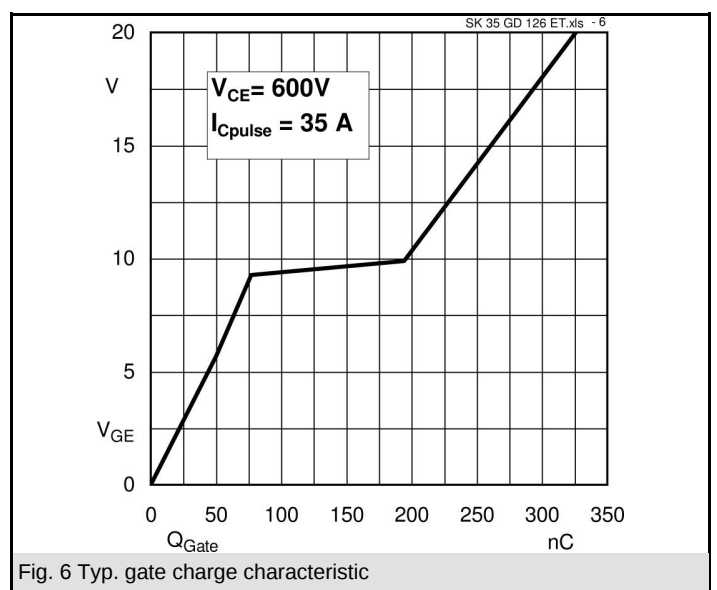
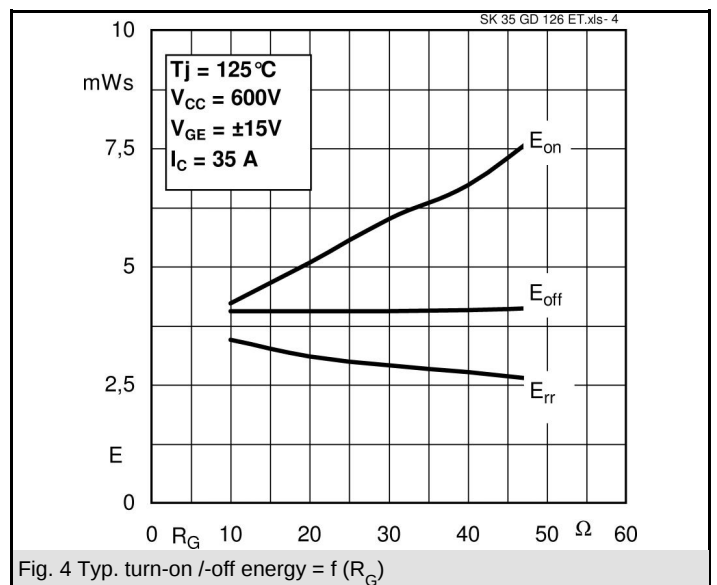
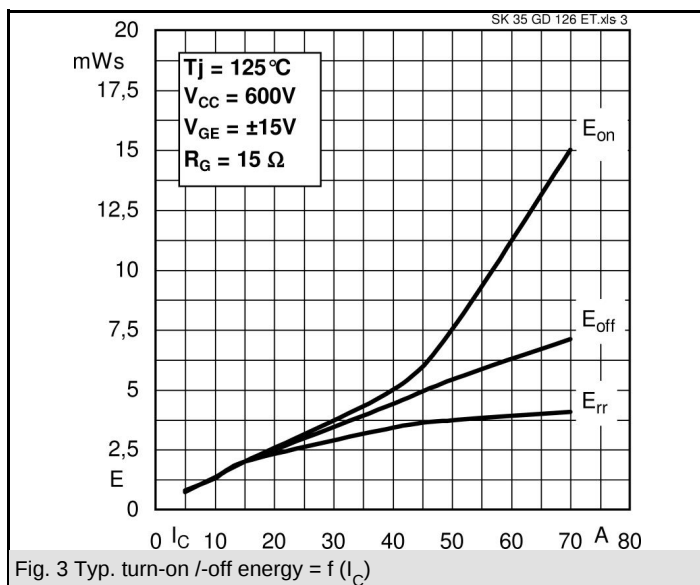
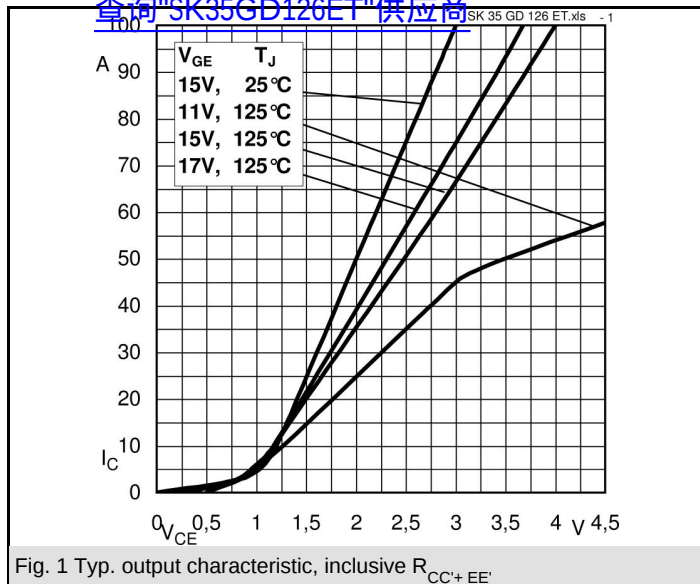
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 35 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,8	2,1	V
		T _j = 125 °C _{chiplev.}		1,8		V
V _{F0}		T _j = 25 °C		1	1,1	V
		T _j = 125 °C		0,8		V
r _F		T _j = 25 °C		23	29	mΩ
		T _j = 125 °C		31		mΩ
I _{RRM}	I _{Fnom} = 35 A di/dt = -1330 A/μs V _{CC} = 600V	T _j = 125 °C		43		A
Q _{rr}				7		μC
E _{rr}				2,9		mJ
R _{th(j-s)D}	per diode				1,7	K/W
M _s	to heat sink		2,25		2,5	Nm
w				30		g
Temperature sensor						
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)			493±5%		Ω

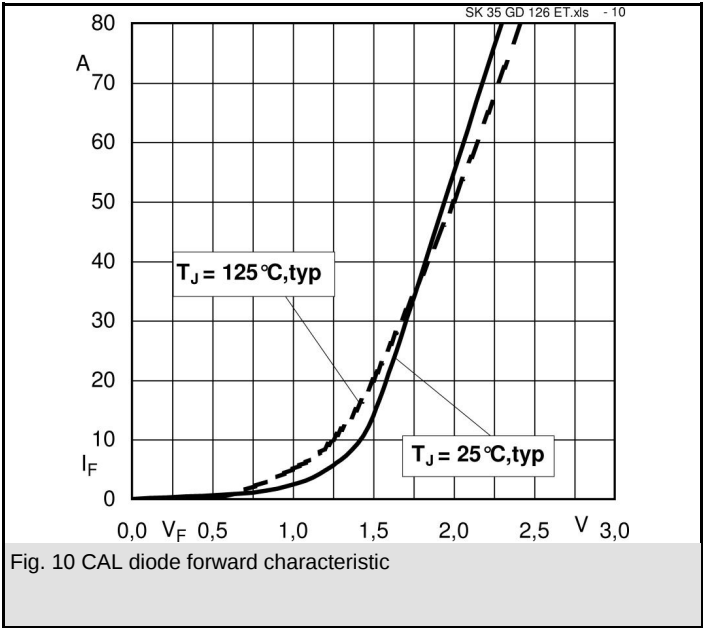
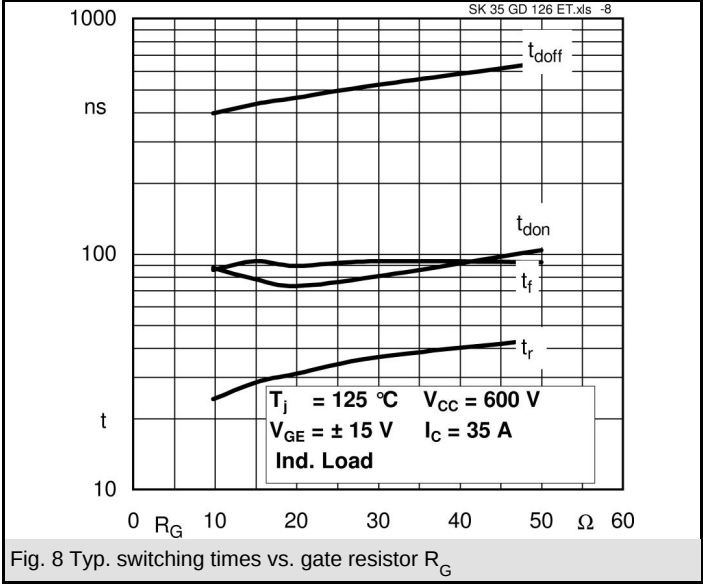
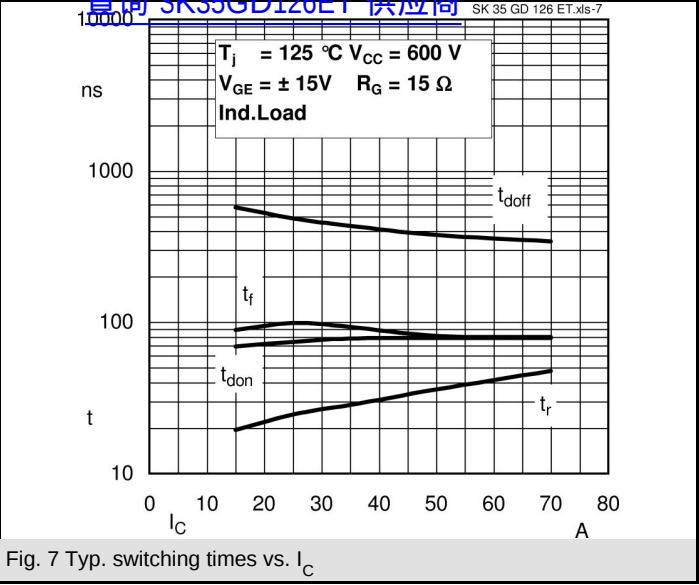
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

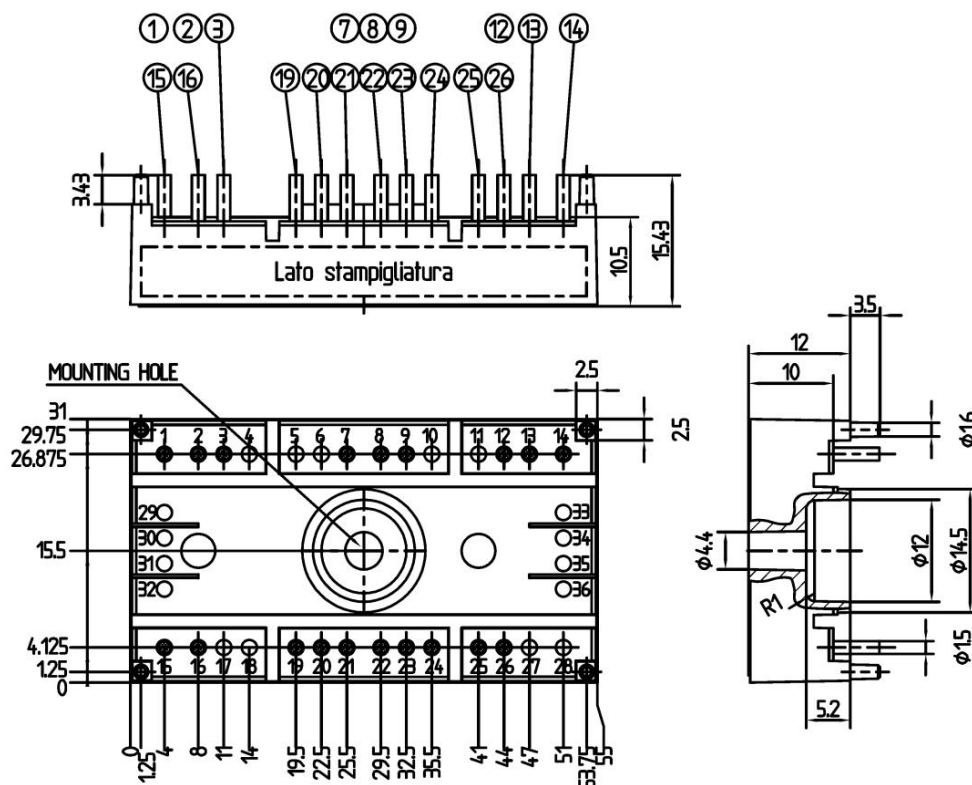
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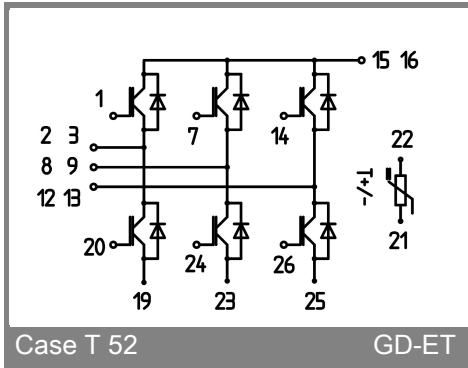


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Case T52 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 52

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